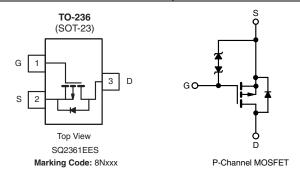


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Vishay Siliconix

Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	- 60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.150				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.200				
I _D (A)	- 2.5				



FEATURES

• TrenchFET® Power MOSFET

• Typical ESD Protection: 800 V

AEC-Q101 Qualified

• 100 % R_g and UIS Tested

Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	SQ2361EES-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	- 60	V	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C		- 2.5		
	T _C = 125 °C	- I _D	- 1.4		
Continuous Source Current (Diode Conduction)		I _S	- 2.5	Α	
Pulsed Drain Current ^a		I _{DM}	- 10		
Single Pulse Avalanche Current		I _{AS}	- 15		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	11	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	Б	2	W	
	T _C = 125 °C	- P _D	0.67	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient P	PCB Mount ^b	R_{thJA}	175	°C/W	
Junction-to-Foot (Drain)		R_{thJF}	75	C/VV	

Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. When mounted on 1" square PCB (FR-4 material).



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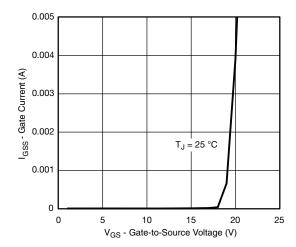
PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static						1		
Drain-Source Breakdown Voltage	V_{DS}	V _{GS} =	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = - 250 μA	- 1.5	-	- 2.5	V	
Gate-Source Leakage		V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 30	mA	
	I _{GSS}	V _{DS} =	= 0 V, V _{GS} = ± 8 V	-	-	± 2		
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V _{DS} = - 60 V	-	-	- 1	1	
	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 60 V, T _J = 125 °C	-	-	- 50	- μA -	
		V _{GS} = 0 V	V _{DS} = - 60 V, T _J = 175 °C	-	-	- 150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	$V_{DS} \le -5 V$	- 10	-	-	Α	
		V _{GS} = - 10 V	I _D = - 2.4 A	-	0.115	0.150	Ω	
Durin On and On Olate Beside and		V _{GS} = - 10 V	I _D = - 2.4 A , T _J = 125 °C	-	-	0.260		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 2.4 A, T _J = 175 °C	-	-	0.310		
		V _{GS} = - 4.5 V	I _D = - 1.8 A	-	0.160	0.200		
Forward Transconductanceb	9 _{fs}	V _{DS} = - 10 V, I _D = - 2 A		-	5	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	435	545		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = -30 \text{ V}, f = 1 \text{ MHz}$	-	55	70	pF	
Reverse Transfer Capacitance	C _{rss}			-	40	50		
Total Gate Charge ^c	Q_g		V _{DS} = - 30 V, I _D = - 6 A	-	11.2	17	nC	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V		-	1.6	=-		
Gate-Drain Charge ^c	Q _{gd}			-	3.2	=-		
Gate Resistance	R_g		f = 1 MHz		5.4	8.1	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	7	11		
Rise Time ^c	t _r	V _{DD} =	$V_{DD} = -30 \text{ V}, R_{L} = 20 \Omega$		8	12	- ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ - 1.5 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	19	29		
Fall Time ^c	t _f			-	8	12		
Source-Drain Diode Ratings and Chara	acteristics ^b	•						
Pulsed Current ^a	I _{SM}			_	_	- 10	Α	
i dioca odiront	·SIVI							

Notes

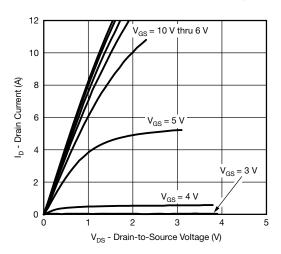
- a. Pulse test; pulse width $\leq 300~\mu s,\,duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

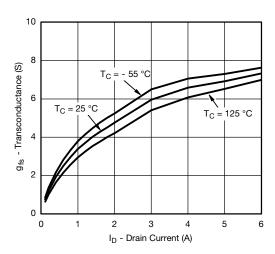
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



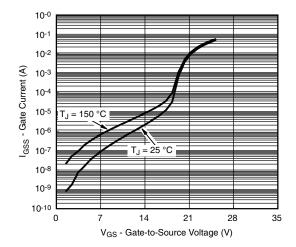
Gate Current vs. Gate-Source Voltage



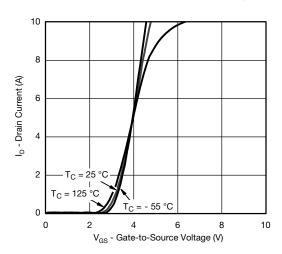
Output Characteristics



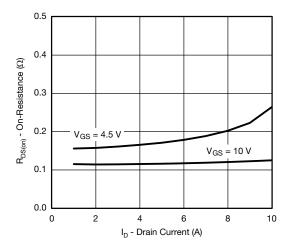
Transconductance



Gate Current vs. Gate-Source Voltage

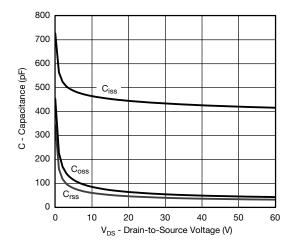


Transfer Characteristics

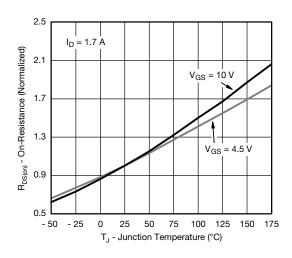


On-Resistance vs. Drain Current

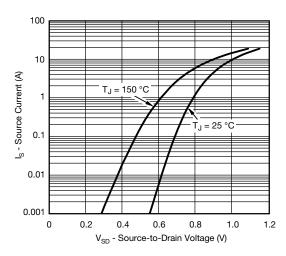
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



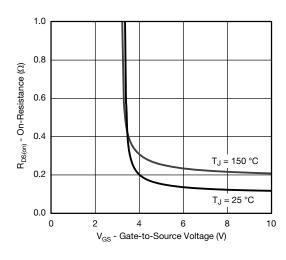
Capacitance



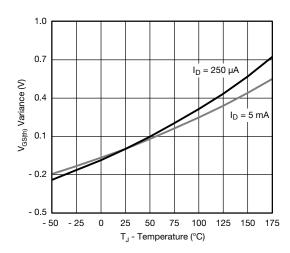
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

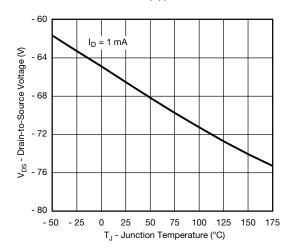


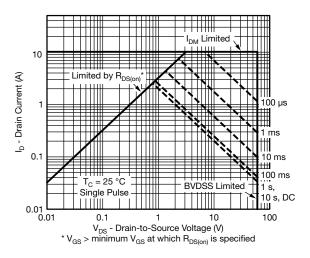
On-Resistance vs. Gate-Source Voltage

Threshold Voltage



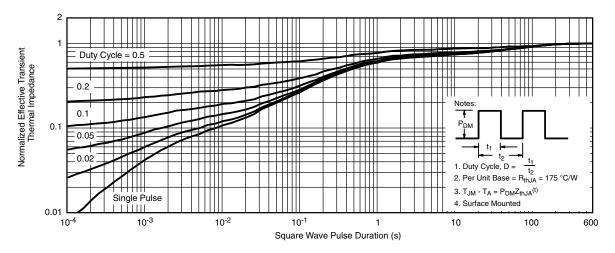
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)





Drain Source Breakdown vs. Junction Temperature

Safe Operating Area

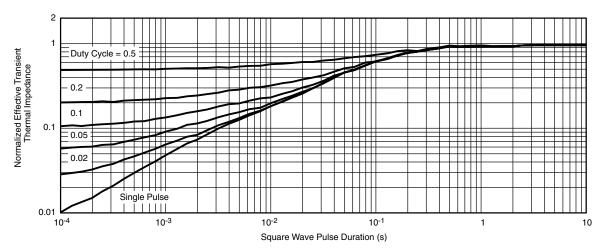


Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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